

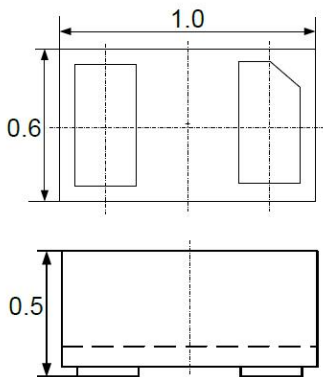
Description

The SEU1501P1 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The SEU1501P1 has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 15\text{kV}$ air and $\pm 8\text{kV}$ contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make SEU1501P1 an ideal choice to protect cell phone and high-power USB.

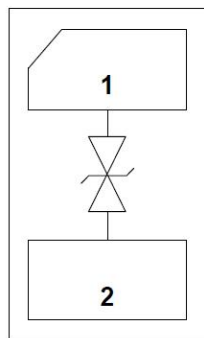
Features

- Ultra small package: 1.0x0.6x0.5mm
- Protects one data or power line
- Working voltage: 15V
- Ultra low capacitance: 0.3pF typical
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 15\text{kV}$
 - Contact discharge: $\pm 8\text{kV}$
 - IEC61000-4-5 (Lightning) 2.5A (8/20us)
- RoHS Compliant

Dimensions & Symbol (Unit: mm Max)



Package Dimensions



Circuit and Pin Schematic

Mechanical Characteristics

- Package: DFN1006-2 (1.0x0.6x0.5mm)
- Lead Finish: NiPdAu
- Case Material: "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Serial ATA
- MDDI Ports
- USB Ports
- PCI Express and Serial SATA Ports

Marking Information



Details marking code reference specification of approval list

Ordering Information

Part Number	Packaging	Reel Size
SEU1501P1	10000/Tape & Reel	7 inch

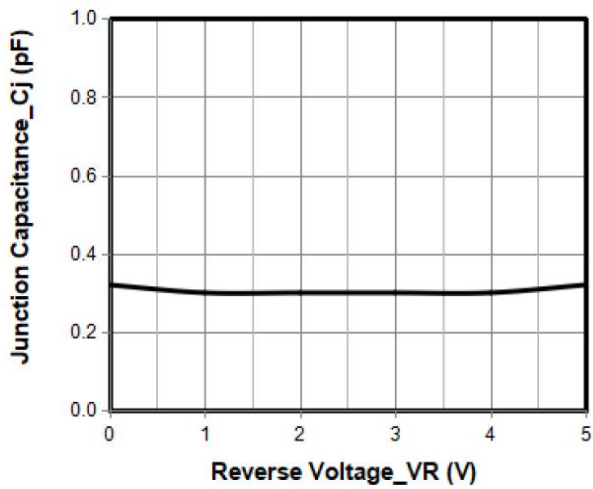
Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P_{ppp}	90	W
Peak Pulse Current (8/20μs)	I_{pp}	2.5	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	±15	kV
ESD per IEC 61000-4-2 (Contact)		±8	
Operating Temperature Range	T_J	-55 to +125	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

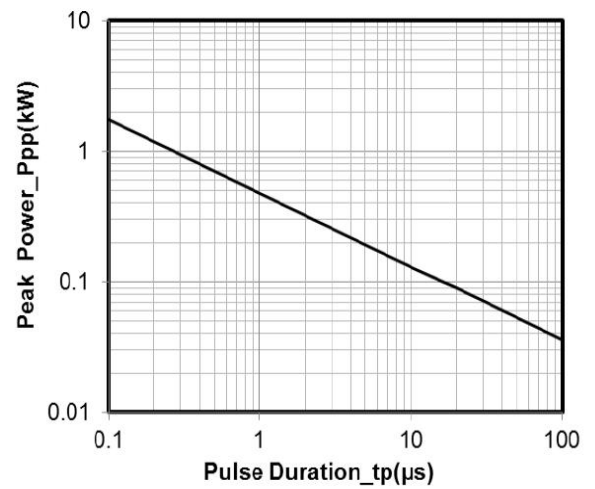
Electrical Characteristics ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			15	V	
Breakdown Voltage	V_{BR}	16.7			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.2	μA	$V_{RWM} = 15\text{V}$
Clamping Voltage	V_C			26	V	$I_{PP} = 1\text{A}$ (8 x 20μs pulse)
Clamping Voltage	V_C			35	V	$I_{PP} = 2.5\text{A}$ (8 x 20μs pulse)
Junction Capacitance	C_J		0.3	0.5	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

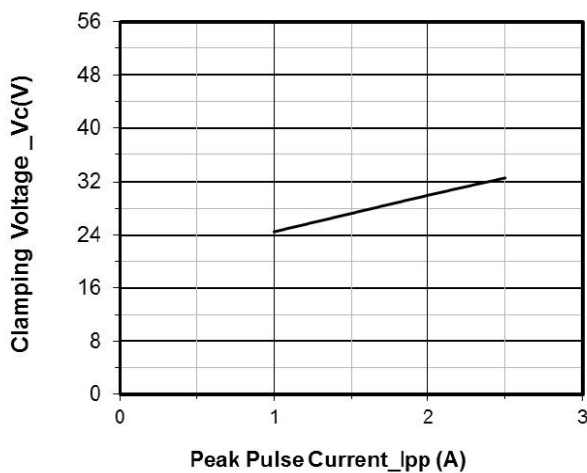
Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)



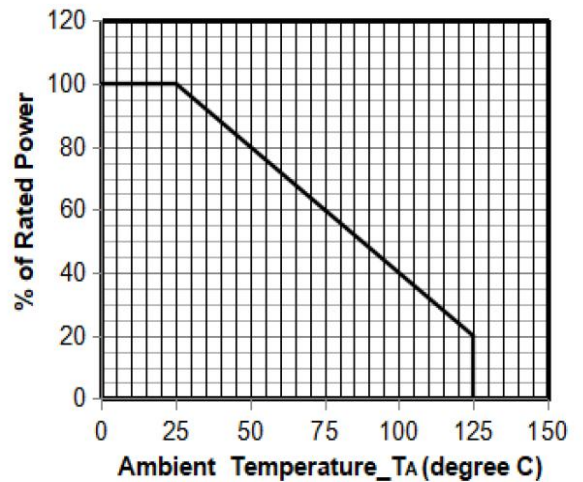
Junction Capacitance vs. Reverse Voltage



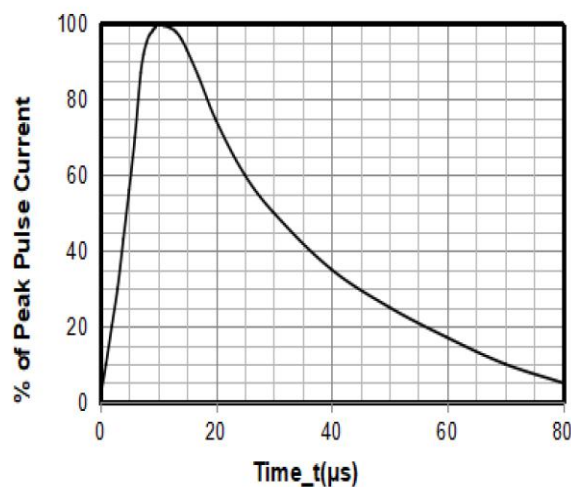
Peak Pulse Power vs. Pulse Time



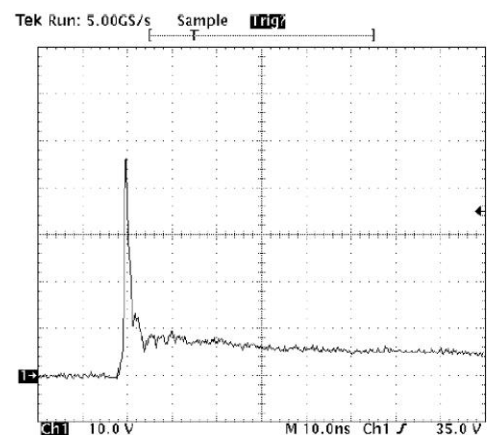
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform



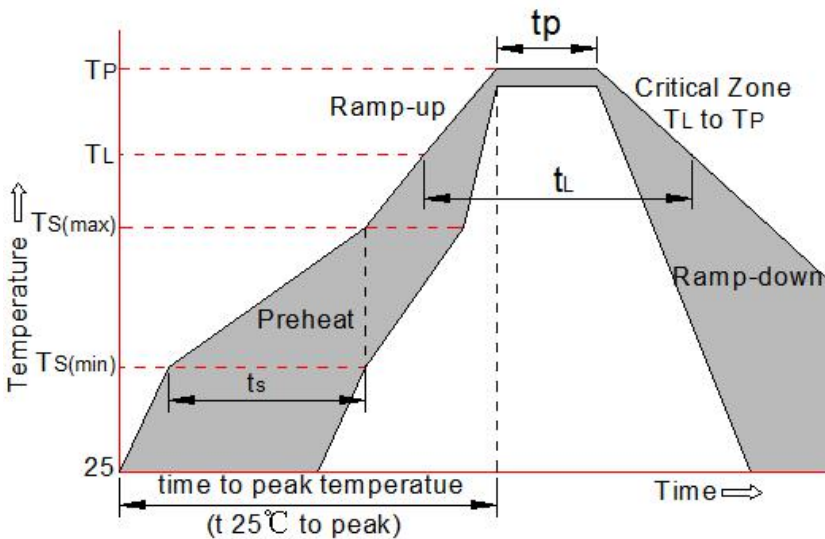
Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

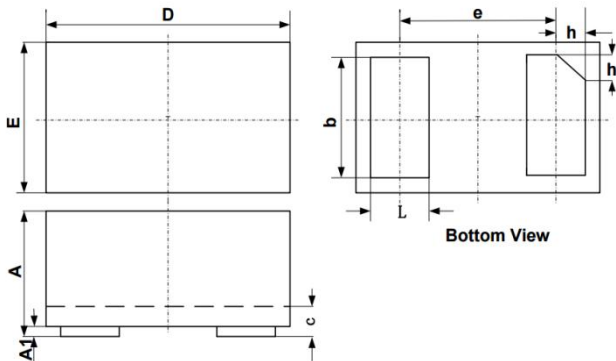
8 kV Contact per IEC61000-4-2

Soldering Parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

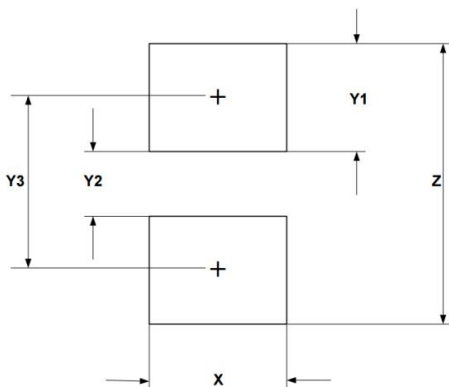


Package Mechanical Data



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052

Contact Information

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